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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	20480
Number of I/O	189
Number of Gates	116000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP Exposed Pad
Supplier Device Package	240-RQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50vrc240-2

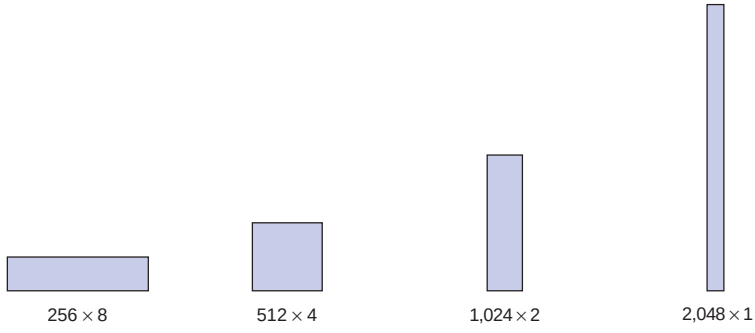
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement a 4 × 4 multiplier with eight inputs and eight outputs. Parameterized functions such as LPM functions can automatically take advantage of the EAB.

The EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These FPGA RAM blocks contain delays that are less predictable as the size of the RAM increases. In addition, FPGA RAM blocks are prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the EAB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. A circuit using the EAB's self-timed RAM need only meet the setup and hold time specifications of the global clock.

When used as RAM, each EAB can be configured in any of the following sizes: 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. See Figure 2.

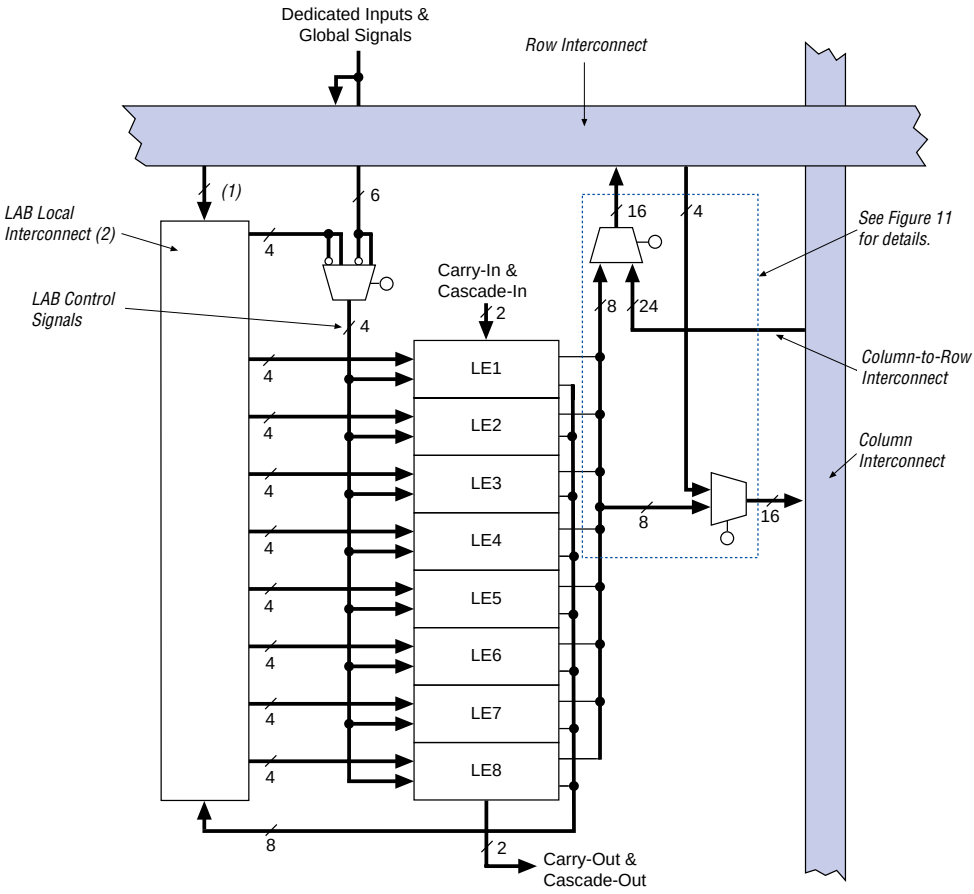
Figure 2. EAB Memory Configurations



Logic Array Block

Each LAB consists of eight LEs, their associated carry and cascade chains, LAB control signals, and the LAB local interconnect. The LAB provides the coarse-grained structure to the FLEX 10K architecture, facilitating efficient routing with optimum device utilization and high performance. See Figure 5.

Figure 5. FLEX 10K LAB



Notes:

(1) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 22 inputs to the LAB local interconnect channel from the row; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 26.

(2) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 30 LAB local interconnect channels; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 34 LABs.

LE Operating Modes

The FLEX 10K LE can operate in the following four modes:

- Normal mode
- Arithmetic mode
- Up/down counter mode
- Clearable counter mode

Each of these modes uses LE resources differently. In each mode, seven available inputs to the LE—the four data inputs from the LAB local interconnect, the feedback from the programmable register, and the carry-in and cascade-in from the previous LE—are directed to different destinations to implement the desired logic function. Three inputs to the LE provide clock, clear, and preset control for the register. The Altera software, in conjunction with parameterized functions such as LPM and DesignWare functions, automatically chooses the appropriate mode for common functions such as counters, adders, and multipliers. If required, the designer can also create special-purpose functions which use a specific LE operating mode for optimal performance.

The architecture provides a synchronous clock enable to the register in all four modes. The Altera software can set `DATA1` to enable the register synchronously, providing easy implementation of fully synchronous designs.

Figure 9 shows the LE operating modes.

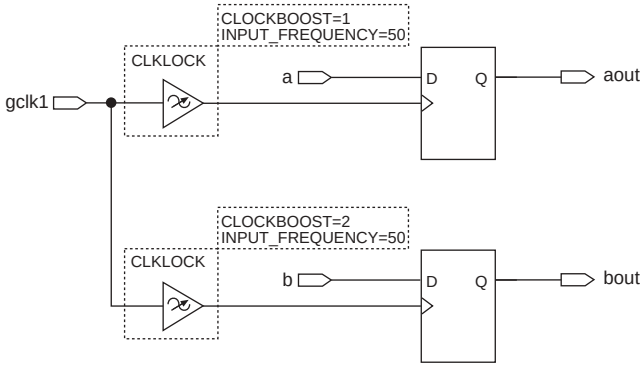
Table 8. EPF10K10, EPF10K20, EPF10K30, EPF10K40 & EPF10K50 Peripheral Bus Sources

Peripheral Control Signal	EPF10K10 EPF10K10A	EPF10K20	EPF10K30 EPF10K30A	EPF10K40	EPF10K50 EPF10K50V
OE0	Row A	Row A	Row A	Row A	Row A
OE1	Row A	Row B	Row B	Row C	Row B
OE2	Row B	Row C	Row C	Row D	Row D
OE3	Row B	Row D	Row D	Row E	Row F
OE4	Row C	Row E	Row E	Row F	Row H
OE5	Row C	Row F	Row F	Row G	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A	Row A	Row B	Row A
CLKENA1/OE6/GLOBAL1	Row A	Row B	Row B	Row C	Row C
CLKENA2/CLR0	Row B	Row C	Row C	Row D	Row E
CLKENA3/OE7/GLOBAL2	Row B	Row D	Row D	Row E	Row G
CLKENA4/CLR1	Row C	Row E	Row E	Row F	Row I
CLKENA5/CLK1/GLOBAL3	Row C	Row F	Row F	Row H	Row J

Table 9. EPF10K70, EPF10K100, EPF10K130V & EPF10K250A Peripheral Bus Sources

Peripheral Control Signal	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
OE0	Row A	Row A	Row C	Row E
OE1	Row B	Row C	Row E	Row G
OE2	Row D	Row E	Row G	Row I
OE3	Row I	Row L	Row N	Row P
OE4	Row G	Row I	Row K	Row M
OE5	Row H	Row K	Row M	Row O
CLKENA0/CLK0/GLOBAL0	Row E	Row F	Row H	Row J
CLKENA1/OE6/GLOBAL1	Row C	Row D	Row F	Row H
CLKENA2/CLR0	Row B	Row B	Row D	Row F
CLKENA3/OE7/GLOBAL2	Row F	Row H	Row J	Row L
CLKENA4/CLR1	Row H	Row J	Row L	Row N
CLKENA5/CLK1/GLOBAL3	Row E	Row G	Row I	Row K

Figure 17. Enabling ClockLock & ClockBoost in the Same Design



To use both the ClockLock and ClockBoost circuits in the same design, designers must use Revision C EPF10K100GC503-3DX devices and MAX+PLUS II software versions 7.2 or higher. The die revision is indicated by the third digit of the nine-digit code on the top side of the device.

Output Configuration

This section discusses the peripheral component interconnect (PCI) pull-up clamping diode option, slew-rate control, open-drain output option, MultiVolt I/O interface, and power sequencing for FLEX 10K devices. The PCI pull-up clamping diode, slew-rate control, and open-drain output options are controlled pin-by-pin via Altera logic options. The MultiVolt I/O interface is controlled by connecting V_{CCIO} to a different voltage than V_{CCINT}. Its effect can be simulated in the Altera software via the **Global Project Device Options** dialog box (Assign menu).

PCI Clamping Diodes

The EPF10K10A and EPF10K30A devices have a pull-up clamping diode on every I/O, dedicated input, and dedicated clock pin. PCI clamping diodes clamp the transient overshoot caused by reflected waves to the V_{CCIO} value and are required for 3.3-V PCI compliance. Clamping diodes can also be used to limit overshoot in other systems.

Clamping diodes are controlled on a pin-by-pin basis via a logic option in the Altera software. When V_{CCIO} is 3.3 V, a pin that has the clamping diode turned on can be driven by a 2.5-V or 3.3-V signal, but not a 5.0-V signal. When V_{CCIO} is 2.5 V, a pin that has the clamping diode turned on can be driven by a 2.5-V signal, but not a 3.3-V or 5.0-V signal. However, a clamping diode can be turned on for a subset of pins, which allows devices to bridge between a 3.3-V PCI bus and a 5.0-V device.

Figure 18 shows the timing requirements for the JTAG signals.

Figure 18. JTAG Waveforms

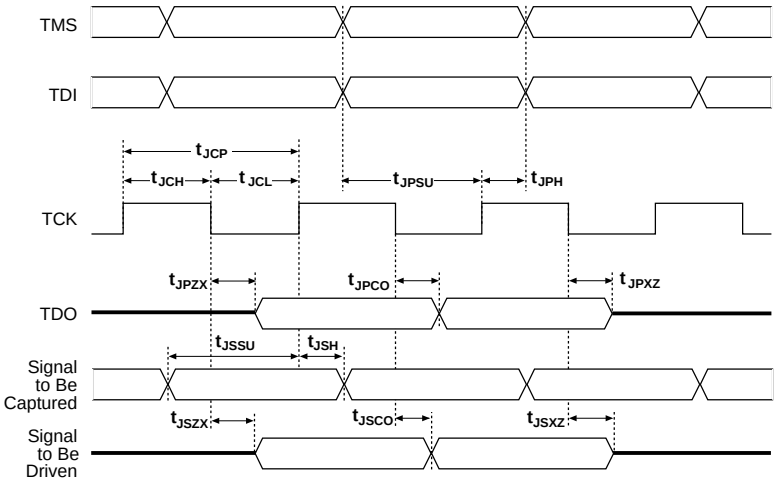


Table 16 shows the timing parameters and values for FLEX 10K devices.

Table 16. JTAG Timing Parameters & Values

Symbol	Parameter	Min	Max	Unit
t_{JCP}	TCK clock period	100		ns
t_{JCH}	TCK clock high time	50		ns
t_{JCL}	TCK clock low time	50		ns
t_{JPSU}	JTAG port setup time	20		ns
t_{JPH}	JTAG port hold time	45		ns
t_{JPCO}	JTAG port clock to output		25	ns
t_{JPZX}	JTAG port high impedance to valid output		25	ns
t_{JPXZ}	JTAG port valid output to high impedance		25	ns
t_{JSSU}	Capture register setup time	20		ns
t_{JSH}	Capture register hold time	45		ns
t_{JSCO}	Update register clock to output		35	ns
t_{JSZX}	Update register high-impedance to valid output		35	ns
t_{JSXZ}	Update register valid output to high impedance		35	ns

Timing simulation and delay prediction are available with the MAX+PLUS II Simulator and Timing Analyzer, or with industry-standard EDA tools. The Simulator offers both pre-synthesis functional simulation to evaluate logic design accuracy and post-synthesis timing simulation with 0.1-ns resolution. The Timing Analyzer provides point-to-point timing delay information, setup and hold time analysis, and device-wide performance analysis.

Figure 24 shows the overall timing model, which maps the possible paths to and from the various elements of the FLEX 10K device.

Figure 24. FLEX 10K Device Timing Model

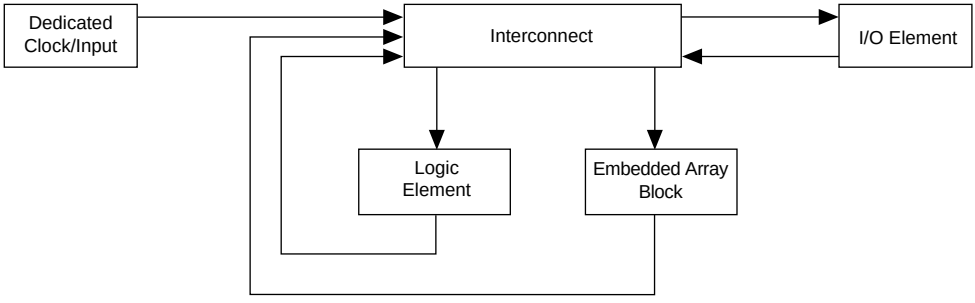


Table 32. LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	Parameter	Conditions
t_{SU}	LE register setup time for data and enable signals before clock; LE register recovery time after asynchronous clear, preset, or load	
t_{H}	LE register hold time for data and enable signals after clock	
t_{PRE}	LE register preset delay	
t_{CLR}	LE register clear delay	
t_{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 33. IOE Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
t_{IOD}	IOE data delay	
t_{IOC}	IOE register control signal delay	
t_{IOCO}	IOE register clock-to-output delay	
t_{IOCOMB}	IOE combinatorial delay	
t_{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t_{IOH}	IOE register hold time for data and enable signals after clock	
t_{IOCLR}	IOE register clear time	
t_{OD1}	Output buffer and pad delay, slow slew rate = off, $V_{CCIO} = V_{CCINT}$	C1 = 35 pF *(2)*
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = low voltage	C1 = 35 pF *(3)*
t_{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{XZ}	IOE output buffer disable delay	
t_{ZX1}	IOE output buffer enable delay, slow slew rate = off, $V_{CCIO} = V_{CCINT}$	C1 = 35 pF *(2)*
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = low voltage	C1 = 35 pF *(3)*
t_{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{INREG}	IOE input pad and buffer to IOE register delay	
t_{IOFD}	IOE register feedback delay	
t_{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Table 35. EAB Timing Macroparameters *Notes (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Table 36. Interconnect Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{DIN2IOE}$	Delay from dedicated input pin to IOE control input	*(7)*
$t_{DCLK2LE}$	Delay from dedicated clock pin to LE or EAB clock	*(7)*
$t_{DIN2DATA}$	Delay from dedicated input or clock to LE or EAB data	*(7)*
$t_{DCLK2IOE}$	Delay from dedicated clock pin to IOE clock	*(7)*
t_{DIN2LE}	Delay from dedicated input pin to LE or EAB control input	*(7)*
$t_{SAMELAB}$	Routing delay for an LE driving another LE in the same LAB	
$t_{SAMEROW}$	Routing delay for a row IOE, LE, or EAB driving a row IOE, LE, or EAB in the same row	*(7)*
$t_{SAMECOLUMN}$	Routing delay for an LE driving an IOE in the same column	*(7)*
$t_{DIFFROW}$	Routing delay for a column IOE, LE, or EAB driving an LE or EAB in a different row	*(7)*
$t_{TWOROWS}$	Routing delay for a row IOE or EAB driving an LE or EAB in a different row	*(7)*
$t_{LEPERIPH}$	Routing delay for an LE driving a control signal of an IOE via the peripheral control bus	*(7)*
$t_{LABCARRY}$	Routing delay for the carry-out signal of an LE driving the carry-in signal of a different LE in a different LAB	
$t_{LABCASC}$	Routing delay for the cascade-out signal of an LE driving the cascade-in signal of a different LE in a different LAB	

Table 37. External Timing Parameters *Notes (8), (10)*

Symbol	Parameter	Conditions
t_{DRR}	Register-to-register delay via four LEs, three row interconnects, and four local interconnects	*(9)*
t_{INSU}	Setup time with global clock at IOE register	
t_{INH}	Hold time with global clock at IOE register	
t_{OUTCO}	Clock-to-output delay with global clock at IOE register	

Table 38. External Bidirectional Timing Parameters *Note (10)*

Symbol	Parameter	Condition
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at adjacent LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at adjacent LE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	
$t_{XZBIDIR}$	Synchronous IOE output buffer disable delay	
$t_{ZXBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate = off	

Table 49. EPF10K30, EPF10K40 & EPF10K50 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		0.4		0.6	ns
t_{IOC}		0.5		0.9	ns
t_{IOCO}		0.4		0.5	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	3.1		3.5		ns
t_{IOH}	1.0		1.9		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		3.3		3.6	ns
t_{OD2}		5.6		6.5	ns
t_{OD3}		7.0		8.3	ns
t_{XZ}		5.2		5.5	ns
t_{ZX1}		5.2		5.5	ns
t_{ZX2}		7.5		8.4	ns
t_{ZX3}		8.9		10.2	ns
t_{INREG}		7.7		10.0	ns
t_{IOFD}		3.3		4.0	ns
t_{INCOMB}		3.3		4.0	ns

Table 67. EPF10K100 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		13.7		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		13.7		17.0		ns
$t_{EABRCREG}$	9.7		9.7		11.9		ns
t_{EABWP}	5.8		5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		7.3		9.0		ns
$t_{EABWCREG}$	13.0		13.0		16.0		ns
t_{EABDD}		10.0		10.0		12.5	ns
$t_{EABDATACO}$		2.0		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	5.5		5.5		5.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.5		5.8		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	2.1		2.1		2.7		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		9.5		9.5		11.8	ns

Table 72. EPF10K50V Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.2		1.6		1.9		2.1	ns
t_{IOC}		0.3		0.4		0.5		0.5	ns
t_{IOCO}		0.3		0.3		0.4		0.4	ns
t_{IOCOMB}		0.0		0.0		0.0		0.0	ns
t_{IOSU}	2.8		2.8		3.4		3.9		ns
t_{IOH}	0.7		0.8		1.0		1.4		ns
t_{IOCLR}		0.5		0.6		0.7		0.7	ns
t_{OD1}		2.8		3.2		3.9		4.7	ns
t_{OD2}		–		–		–		–	ns
t_{OD3}		6.5		6.9		7.6		8.4	ns
t_{XZ}		2.8		3.1		3.8		4.6	ns
t_{ZX1}		2.8		3.1		3.8		4.6	ns
t_{ZX2}		–		–		–		–	ns
t_{ZX3}		6.5		6.8		7.5		8.3	ns
t_{INREG}		5.0		5.7		7.0		9.0	ns
t_{IOFD}		1.5		1.9		2.3		2.7	ns
t_{INCOMB}		1.5		1.9		2.3		2.7	ns

Table 81. EPF10K130V Device EAB Internal Timing Macroparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{EABAA}		11.2		14.2		14.2	ns
$t_{EABRCCOMB}$	11.1		14.2		14.2		ns
$t_{EABRCREG}$	8.5		10.8		10.8		ns
t_{EABWP}	3.7		4.7		4.7		ns
$t_{EABWCCOMB}$	7.6		9.7		9.7		ns
$t_{EABWCREG}$	14.0		17.8		17.8		ns
t_{EABDD}		11.1		14.2		14.2	ns
$t_{EABDATACO}$		3.6		4.6		4.6	ns
$t_{EABDATASU}$	4.4		5.6		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.4		5.6		5.6		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	4.6		5.9		5.9		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.9		5.0		5.0		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		11.1		14.2		14.2	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 92 through 98 show EPF10K30A device internal and external timing parameters.

Table 92. EPF10K30A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.8		1.1		1.5	ns
t_{CLUT}		0.6		0.7		1.0	ns
t_{RLUT}		1.2		1.5		2.0	ns
t_{PACKED}		0.6		0.6		1.0	ns
t_{EN}		1.3		1.5		2.0	ns
t_{CICO}		0.2		0.3		0.4	ns
t_{CGEN}		0.8		1.0		1.3	ns
t_{CGENR}		0.6		0.8		1.0	ns
t_{CASC}		0.9		1.1		1.4	ns
t_{C}		1.1		1.3		1.7	ns
t_{CO}		0.4		0.6		0.7	ns
t_{COMB}		0.6		0.7		0.9	ns
t_{SU}	0.9		0.9		1.4		ns
t_{H}	1.1		1.3		1.7		ns
t_{PRE}		0.5		0.6		0.8	ns
t_{CLR}		0.5		0.6		0.8	ns
t_{CH}	3.0		3.5		4.0		ns
t_{CL}	3.0		3.5		4.0		ns

Table 93. EPF10K30A Device IOE Timing Microparameters *Note (1)* **(Part 1 of 2)**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		2.2		2.6		3.4	ns
t_{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		0.2		0.2		0.3	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	1.4		1.7		2.2		ns

Table 100. EPF10K100A Device IOE Timing Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{IOD}		2.5		2.9		3.4	ns
t_{IOC}		0.3		0.3		0.4	ns
t_{IOCO}		0.2		0.2		0.3	ns
t_{IOCOMB}		0.5		0.6		0.7	ns
t_{IOSU}	1.3		1.7		1.8		ns
t_{IOH}	0.2		0.2		0.3		ns
t_{IOCLR}		1.0		1.2		1.4	ns
t_{OD1}		2.2		2.6		3.0	ns
t_{OD2}		4.5		5.3		6.1	ns
t_{OD3}		6.8		7.9		9.3	ns
t_{XZ}		2.7		3.1		3.7	ns
t_{ZX1}		2.7		3.1		3.7	ns
t_{ZX2}		5.0		5.8		6.8	ns
t_{ZX3}		7.3		8.4		10.0	ns
t_{INREG}		5.3		6.1		7.2	ns
t_{IOFD}		4.7		5.5		6.4	ns
t_{INCOMB}		4.7		5.5		6.4	ns

Table 103. EPF10K100A Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.8		5.4		6.0	ns
t_{DIN2LE}		2.0		2.4		2.7	ns
$t_{DIN2DATA}$		2.4		2.7		2.9	ns
$t_{DCLK2IOE}$		2.6		3.0		3.5	ns
$t_{DCLK2LE}$		2.0		2.4		2.7	ns
$t_{SAMELAB}$		0.1		0.1		0.1	ns
$t_{SAMEROW}$		1.5		1.7		1.9	ns
$t_{SAMECOLUMN}$		5.5		6.5		7.4	ns
$t_{DIFFROW}$		7.0		8.2		9.3	ns
$t_{TWOROWS}$		8.5		9.9		11.2	ns
$t_{LEPERIPH}$		3.9		4.2		4.5	ns
$t_{LABCARRY}$		0.2		0.2		0.3	ns
$t_{LABCASC}$		0.4		0.5		0.6	ns

Table 104. EPF10K100A Device External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		12.5		14.5		17.0	ns
t_{INSU} *(2)*, *(3)*	3.7		4.5		5.1		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.3	2.0	6.1	2.0	7.2	ns

Table 105. EPF10K100A Device External Bidirectional Timing Parameters *Note (1)*

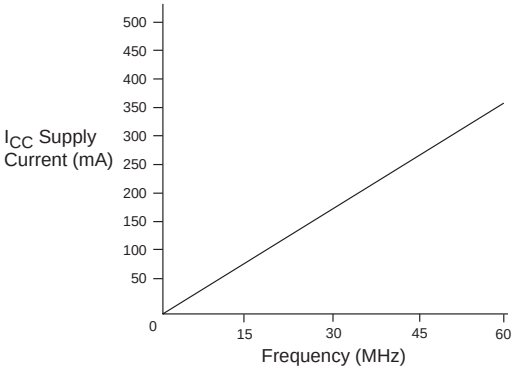
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.9		5.8		6.8		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.3	2.0	6.1	2.0	7.2	ns
$t_{XZBIDIR}$		7.4		8.6		10.1	ns
$t_{ZXBIDIR}$		7.4		8.6		10.1	ns

Table 108. EPF10K250A Device EAB Internal Microparameters *Note (1)*

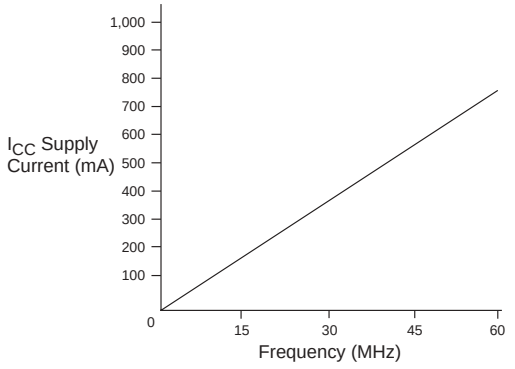
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.3		1.5		1.7	ns
$t_{EABDATA2}$		1.3		1.5		1.7	ns
t_{EABWE1}		0.9		1.1		1.3	ns
t_{EABWE2}		5.0		5.7		6.7	ns
t_{EABCLK}		0.6		0.7		0.8	ns
t_{EABCO}		0.0		0.0		0.0	ns
$t_{EABBYPASS}$		0.1		0.1		0.2	ns
t_{EABSU}	3.8		4.3		5.0		ns
t_{EABH}	0.7		0.8		0.9		ns
t_{AA}		4.5		5.0		5.9	ns
t_{WP}	5.6		6.4		7.5		ns
t_{WDSU}	1.3		1.4		1.7		ns
t_{WDH}	0.1		0.1		0.2		ns
t_{WASU}	0.1		0.1		0.2		ns
t_{WAH}	0.1		0.1		0.2		ns
t_{WO}		4.1		4.6		5.5	ns
t_{DD}		4.1		4.6		5.5	ns
t_{EABOUT}		0.1		0.1		0.2	ns
t_{EABCH}	2.5		3.0		3.5		ns
t_{EABCL}	5.6		6.4		7.5		ns

Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 1 of 3)

EPF10K10



EPF10K20



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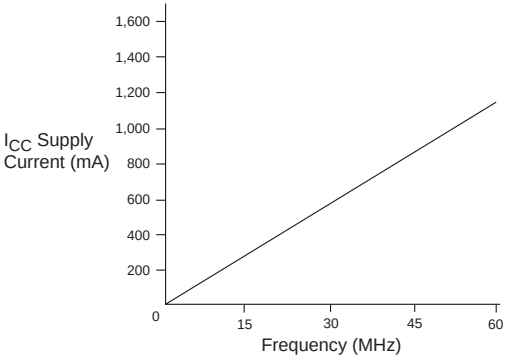

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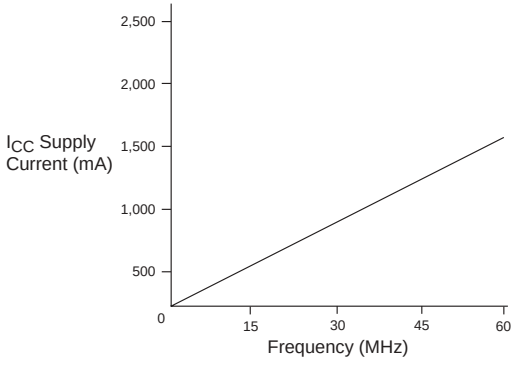
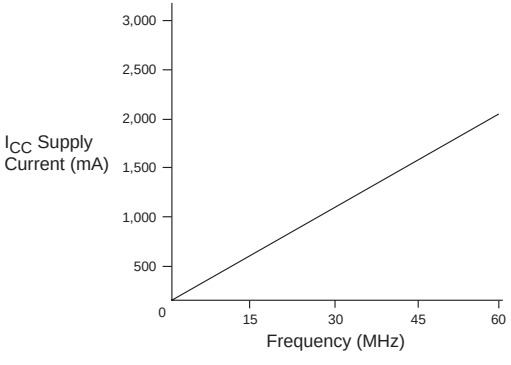


EPF10K50



EPF10K70

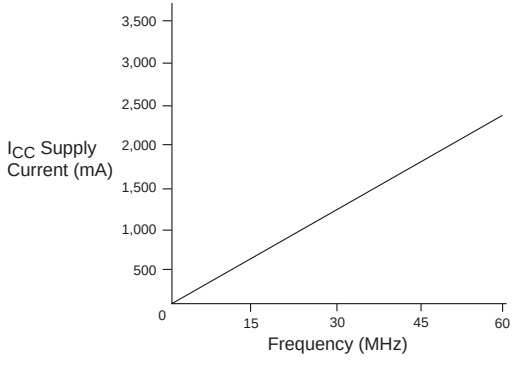
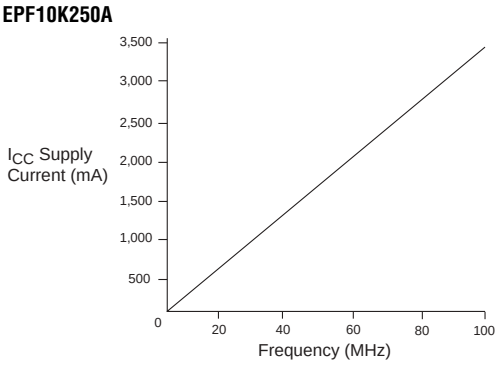


Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 3 of 3)



Configuration & Operation

The FLEX 10K architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

See *Application Note 116 (Configuring APEX 20K, FLEX 10K & FLEX 6000 Devices)* for detailed descriptions of device configuration options, device configuration pins, and for information on configuring FLEX 10K devices, including sample schematics, timing diagrams, and configuration parameters.

Operating Modes

The FLEX 10K architecture uses SRAM configuration elements that require configuration data to be loaded every time the circuit powers up. The process of physically loading the SRAM data into the device is called *configuration*. Before configuration, as VCC rises, the device initiates a Power-On Reset (POR). This POR event clears the device and prepares it for configuration. The FLEX 10K POR time does not exceed 50 µs.

During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.